

## GS2M

### 2.0AMPS.GLASS PASSIVATED SURFACE MOUNT RECTIFIERS

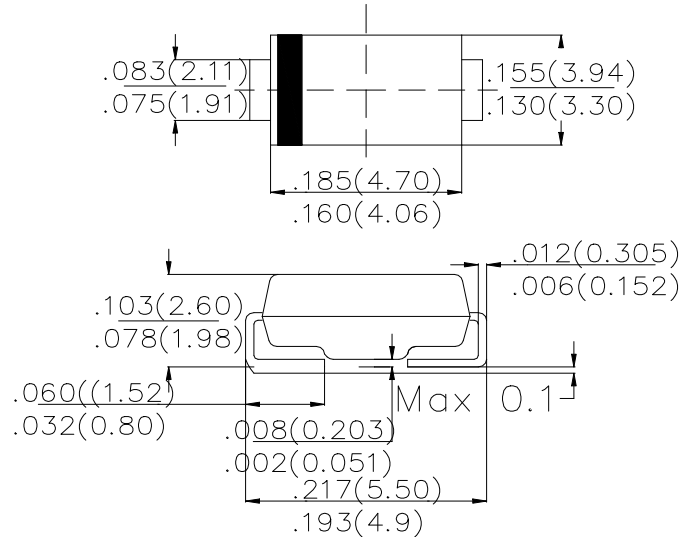
#### FEATURE

- . High current capability
- . Low forward voltage drop
- . Low power loss, high efficiency
- . High surge capability
- . High temperature soldering guaranteed:  
260°C/10 seconds at terminals.
- . For surface mounted application.
- . Easy pick and place.

#### MECHANICAL DATA

- . Case: Molded plastic
- . Epoxy: UL94V-0 rate flame retardant
- . Lead: MIL-STD- 202E, Method 208 guaranteed
- . Polarity:Color band denotes cathode end
- . Packaging:12mm tape per EIA STD RS-481

#### SMB (DO-214AA)



Dimensions in inches and (millimeters)

### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60Hz,resistive or inductive load.For capacitive load, derate current by 20%

Type Number	SYMBOL	GS2M	units
Maximum Recurrent Peak Reverse Voltage	$V_{RRM}$	1000	V
Maximum RMS Voltage	$V_{RMS}$	700	V
Maximum DC blocking Voltage	$V_{DC}$	1000	V
Maximum Average Forward Rectified Current at $T_L=90^\circ\text{C}$	$I_{F(AV)}$	2.0	A
Non-repetitive forward surge current 8.3ms half sine-wave	$I_{FSM}$	60.0	A
Maximum Forward Voltage at 2.0 A DC	$V_F$	1.1	V
Maximum DC Reverse Current @ $T_A=25^\circ\text{C}$ at rated DC blocking voltage @ $T_A=100^\circ\text{C}$	$I_R$	5.0 100.0	$\mu\text{A}$
Typical Junction Capacitance (Note1)	$C_J$	30	pF
Maximum Reverse Recovery Time (Note 2)	$t_{rr}$	4000	nS
Typical Thermal Resistance (Note 3)	$R_{(JA)}$	75	$^\circ\text{C}/\text{W}$
	$R_{(JC)}$	21	$^\circ\text{C}/\text{W}$
Storage Temperature	$T_{STG}$	-55 to +150	$^\circ\text{C}$
Operation Junction Temperature	$T_J$	-55 to +150	$^\circ\text{C}$

#### Note:

1. Measured at 1.0 MHz and applied reverse voltage of 4.0Vdc
2. Reverse Recovery test Condition:  $I_f=0.5\text{A}$ ,  $I_R=1.0\text{A}$ ,  $IRR=0.25\text{A}$
3. Measured on P.C.Board with  $0.2 \times 0.2''$  ( $5.0 \times 5.0\text{mm}$ ) Copper Pad Areas.

**RATING AND CHARACTERISTIC CURVES (GS2M)**

FIG.1-TYPICAL FORWARD CURRENT DERATING CURVE

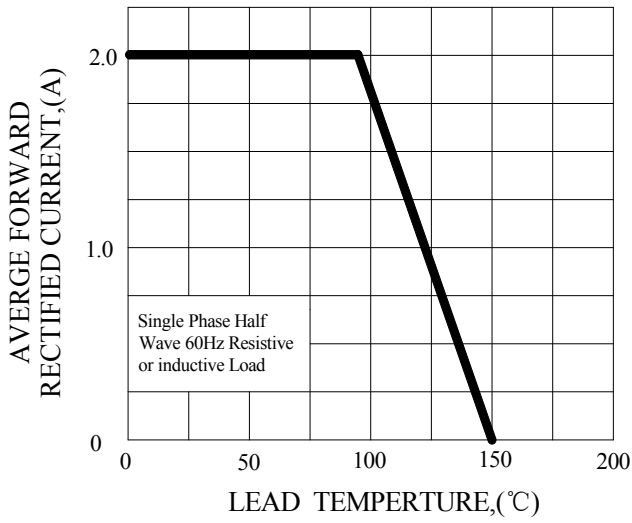


FIG.2-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

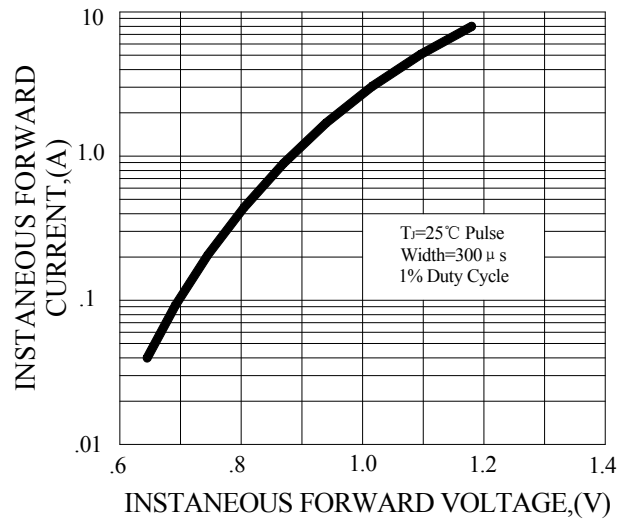


FIG.3-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

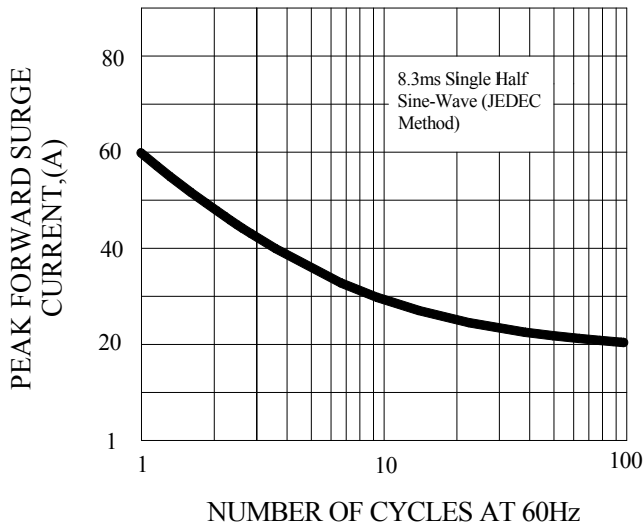


FIG.4-TYPICAL REVERSE CHARACTERISTICS

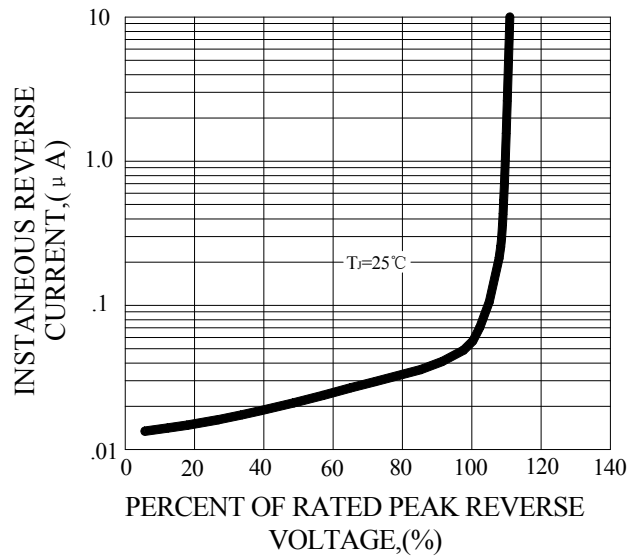
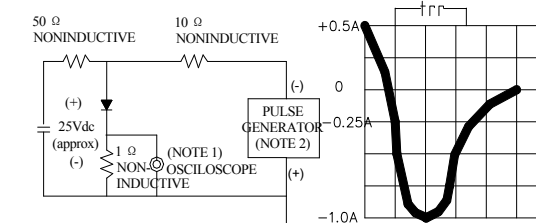


FIG.5-TEST CIRCUIT DIAGRAM AND REVERSE RECOVERY TIME CHARACTERISTIC



NOTES:1. Rise Time=7ns max, Input Impedance= 1 megohm,22pF.  
2. Rise Time=10ns max, Source Impedance= 50 ohms.

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